

Docket No. 5230

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

ANISUL KHAN et al

Confirmation No. 4319

Serial No.: 09/866,313

Examiner: Charlotte A. Brown

Filed: May 24, 2001

Group Art Unit: 1765

For: METHOD OF ELIMINATING NOTCHING
WHEN ANISOTROPICALLY ETCHING
SMALL LINEWIDTH OPENINGS IN
SILICON ON INSULATOR

RESPONSE UNDER 37 CFR 1.115

To: Assistant Commissioner for Patents
Washington, DC 20231

Sir:

In response to the office action of June 28, 2002, please
amend the above-identified application as follows:

IN THE SPECIFICATION

Substitute the following for the paragraph beginning on page 9
line 14.

A1 --In this Example, no bias power was used during the deposition
steps, but 30 Watts of pulsed bias power was used during the etch
steps, again using a duty cycle of 35% and a period of 6
milliseconds. The average power delivered was 6 Watts.--

#10/A
wa
4/4/03

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GROUP 1700